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FXLA102

Low-Voltage Dual-Supply 2-Bit Voltage Translator with Configurable Voltage Supplies and Signal Levels, 3-State Outputs, and Auto Direction Sensing

Features

- Bi-Directional Interface between Two Levels: from 1.1 V to 3.6V
- Fully Configurable: Inputs and Outputs Track V_{CC}
 Level
- Non-Preferential Power-Up; Either V_{CC} May Be Powered Up First
- Outputs Switch to 3-State if Either V_{CC} is at GND
- Pow er-Off Protection
- Bus-Hold on Data Inputs Eliminates the Need for Pull-Up Resistors; Do Not Use Pull-Up Resistors on A or B Ports
- Control Input (/OE) Referenced to V_{CCA} Voltage
- Packaged in MicroPak[™] 8 (1.6 mm x 1.6 mm)
- Direction Control Not Necessary
- 100 Mbps Throughput when Translating Between
 1.8 V and 2.5 V
- ESD Protection Exceeds:
 - 15 kV HBM ((B Port I/O to GND) per JESD22-A114 & Mil Std 883e 3015.7)
 - 8 kV HBM ((A Port I/O to GND) per JESD22-A114 & Mil Std 883e 3015.7)
 - 2 kV CDM (per ESD STM 5.3)

Description

The FXLA102 is a configurable dual-voltage supply translator for both uni-directional and bi-directional voltage translation between two logic levels. The device allows translation between voltages as high as 3.6 V to as low as 1.1 V. The A port tracks the $V_{\rm CCA}$ level and the B port tracks the $V_{\rm CCB}$ level. This allows for bi-directional voltage translation over a variety of voltage levels: 1.2 V, 1.5 V, 1.8 V, 2.5 V, and 3.3 V.

The device remains in three-state as long as either $V_{\rm CC}=0~V$, allowing either $V_{\rm CC}$ to be powered up first. Internal power-down control circuits place the device in 3-state if either $V_{\rm CC}$ is removed.

The /OE input, when HIGH, disables both the A and B ports by placing them in a 3-state condition. The /OE input is supplied by $V_{\rm CCA}$.

The FXLA102 supports bi-directional translation without the need for a direction control pin. The two ports of the device have auto-direction sense capability. Either port may sense an input signal and transfer it as an output signal to the other port.

Ordering Information

Part Number	Top Mark	Operating Temperature Range	Package	Packing Method
FXLA102L8X	XF	-40 to 85°C	8-Lead MicroPak™ 1.6 mm x 1.6 mm Package	5 K Units Tape and Reel

Pin Configuration

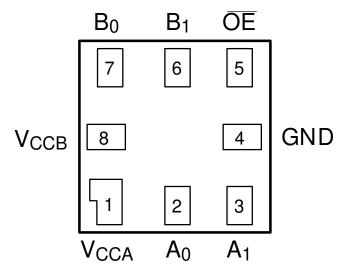


Figure 1. Pin Configuration (Top Through View)

Pin Definitions

Pin#	Name	Description
1	V _{CCA}	A-Side Pow er Supply
2	A ₀	A Side Input or 3-State Output
3	A ₁	A Side Input or 3-State Output
4	GND	Ground
5	/OE	Output Enable Input
6	B ₁	B Side Input or 3-State Output
7	B ₀	B Side Input or 3-State Output
8	V _{CCB}	B Side Pow er Supply

Functional Diagram

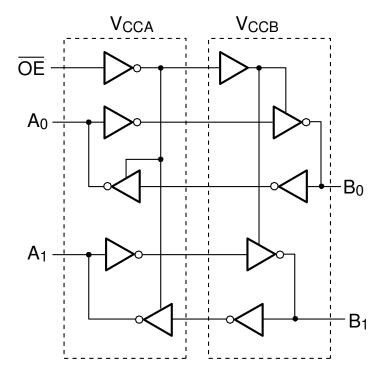


Figure 2. Functional Diagram

Function Table

Control	Outputs
/OE	
L	Normal Operation
Н	3-State

H = HIGH Logic Level

L = LOW Logic Level

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Conditions	Min.	Max.	Unit
V _{CC}	Supply Voltage	V _{CCA}	-0.5	4.6	V
V GG	Cuppiy Vollage	V _{CCB}	-0.5	4.6	V
Vı	DC Input Voltage	VO Ports A and B	-0.5	4.6	V
VI	DC Input Voltage	Control Input (/OE)	-0.5	4.6	V
		Output 3-State	-0.5	4.6	
Vo	Output Voltage ⁽²⁾	Output Active (A _n)	-0.5	V _{CCA} +0.5	V
		Output Active (B _n)	-0.5	V _{CCB} +0.5	
lık	DC Input Diode Current	V _I <0V		-50	mA
Юк	DC Output Diode Current	V _O <0V		-50	mA
IOK	DC Output blode Current	V _O >V _C C		+50	ША
lon/lol	DC Output Source/Sink Current		-50	+50	mA
lcc	DC V _{CC} or Ground Current (per Supply	Pin)		±100	mA
T _{STG}	Storage Temperature Range		-65	+150	°C
P _D	Pow er Dissipation			5	mW
	Human Body Model, JESD22-A114	B Port I/O to GND		15	
ESD	Tidinan body wodel, JESD22-A114	A Port I/O to GND		8	kV
	Charged Device Model, JESD22-C101			2	

Notes:

- 1. lo absolute maximum ratings must be observed.
- 2. All unused inputs and input/outputs must be held at V_{CCi} or GND.

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. ON Semiconductor does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Conditions	Min.	Max.	Unit
V _{CC}	Pow er Supply	Operating V _{CCA} or V _{CCB}	1.1	3.6	V
V _{IN}	Input Voltage	Ports A and B	0	3.6	V
V IN	input voltage	Control Input (/OE)	0	V _{CCA}	V
		V _{CC} = 3.0 V to 3.6 V		±12	
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		±8	
	Dynamic Output Current IOH/IOL	V _{CC} = 1.65 V to 1.95 V		±5	mA
		$V_{CC} = 1.40 \text{ V to } 1.65 \text{ V}$		±3	
		V _{CC} =1.1 V to 1.4 V		±2	
	Static Output Current	V _{CC} =1.1 V to 3.6 V		±4	μΑ
T _A	Operating Temperature, Free Air		-40	+85	°C
dt/dV	Maximum Input Edge Rate	V _{CCA/B} = 1.1 to 3.6 V		10	ns/V
ΘJA	Thermal Resistance			280	°C/W

Power-Up/Power-Down Sequence

FXL translators offer an advantage in that either V_{CC} may be powered up first. This benefit derives from the chip design. When either V_{CC} is at 0 V, outputs are in a high-impedance state. The control input (/OE) is designed to track the V_{CCA} supply. A pull-up resistor tying /OE to V_{CCA} should be used to ensure that bus contention, excessive currents, or oscillations do not occur during power-up or power-down. The size of the pull-up resistor is based upon the current-sinking capability of the device driving the /OE pin.

The recommended power-up sequence is:

- 1. Apply power to the first V_{CC} .
- 2. Apply power to the second V_{CC} .
- 3. Drive the /OE input LOW to enable the device.

The recommended power-down sequence is:

- 1. Drive /OE input HIGH to disable the device.
- 2. Remove power from either V_{CC} .
- 3. Remove power from other V_{CC}.

Pull-Up/Pull-Down Resistors

<u>Do not use pull-up or pull-down resistors.</u> This device has bus-hold circuits: pull-up or pull-down resistors are not recommended because they interfere with the output state. The current through these resistors may exceed the hold drive, $I_{I(HOLD)}$ and/or $I_{I(OD)}$ bus-hold currents. The bus-hold feature eliminates the need for extra resistors.

DC Electrical Characteristics

T_A=-40 to 85°C.

Symbol	Parameter	Conditions	V _{CCA} (V)	V _{CCB} (V)	Min.	Тур.	Max.	Units			
			2.70 to 3.60		2.00						
			2.30 to 2.70		1.60						
V_{IHA}		Data Inputs An Control Pin /OE	1.65 to 2.30	1.10 to 3.60	.65xV _{CCA}			V			
		3011.101 1 111 7 32	1.40 to 1.65		.65xV _{CCA}						
	High-Level Input Voltage		1.10 to 1.40		.90xV _{CCA}						
	night-Level lilput voltage			2.70 to 3.60	2.00						
						2.30 to 2.70	1.60				
V_{IHB}		Data Inputs B _n	1.10 to 3.60	1.65 to 2.30	.65xV _{CCB}			V			
				1.40 to 1.65	.65xV _{CCB}						
				1.10 to 1.40	.90xV _{CCB}						
			2.70 to 3.60				.80				
			2.30 to 2.70				.70				
V_{ILA}		Data Inputs A _n Control Pin /OE	1.65 to 2.30	1.10 to 3.60			.35xV _{CCA}	٧			
		Sontion I'm 70L	1.40 to 1.65				.35xV _{CCA}				
Low - Level Input \	Laur Laurelhamut Valtage		1.10 to 1.40				.10xV _{CCA}				
	Low-Level input voitage			2.70 to 3.60			.80				
		Data Inputs B _n		2.30 to 2.70			.70				
V_{ILB}			1.10 to 3.60	1.65 to 2.30			.35xV _{CCB}	٧			
			·					1.40 to 1.65			.35xV _{CCB}
				1.10 to 1.40			.10xV _{CCB}				
V _{OHA}	High-Leyel Output	Ι _{ΟΗ} =-4 μΑ	1.10 to 3.60	1.10 to 3.60	V _{CCA} 40			.,			
V _{OHB}	Voltage ⁽³⁾	l _{OH} =-4μ A	1.10 to 3.60	1.10 to 3.60	V _{CCB} 40			V			
Vola	Low -Leyel Output	l _{OL} =4 μA	1.10 to 3.60	1.10 to 3.60			.4	V			
V _{OLB}	Voltage ⁽³⁾	l _{OL} =4 μA	1.10 to 3.60	1.10 to 3.60			.4	V			
		V _{IN} =0.80 V	3.00	3.00	75.0						
		V _{IN} =2.00 V	3.00	3.00	-75.0						
		V _{IN} =0.70 V	2.30	2.30	45.0						
		V _{IN} =1.60 V	2.30	2.30	-45.0						
l _{l(HOLD)} Bu Dri	Bus-Hold Input Minimum	V _{IN} =0.57 V	1.65	1.65	25.0						
	Drive Current	V _{IN} =1.07 V	1.65	1.65	-25.0			μΑ			
		V _{IN} =0.49 V	1.40	1.40	11.0						
		V _{IN} =0.91 V	1.40	1.40	-11.0						
		V _{IN} =0.11 V	1.10	1.10		4.0					
		V _{IN} =0.99 V	1.10	1.10		-4.0					

Continued on following page...

DC Electrical Characteristics (Continued)

T_A=-40 to 85°C.

Symbol	Parameter	Conditions	V _{CCA} (V)	V _{CCB} (V)	Min.	Max.	Units
			3.60	3.60	450.00		
	Bus-Hold Input		2.70	2.70	300.00		1
I _{I(ODH)}	Overdrive High	Data Inputs An, Bn	1.95	1.95	200.00		μΑ
	Current ⁽⁴⁾		1.60	1.60	120.00		1
			1.40	1.40	80.00		1
			3.60	3.60	-450.00		
	Bus-Hold Input		2.70	2.70	-300.00		1
I _{I(ODL)}	Overdrive Low	Data Inputs A _n , B _n	1.95	1.95	-200.00		μΑ
	Current ⁽⁵⁾		1.60	1.60	-120.00		1
			1.40	1.40	-80.00		
l _i	Input Leakage Current	Control Inputs /OE, V _I =V _{CCA} or GND	1.10 to 3.60	3.60		±1.0	μΑ
l	Pow er-Off Leakage	A _n Port V _O =0V to 3.6 V	0	3.6		±2.0	
loff	Current	B _n Port V _O =0V to 3.6 V	3.60	0		±2.0	μΑ
		Data Outputs A _n , B _n V _O =0 V or 3.6 V, /OE=V _{IH}	3.60	3.60		±5.0	
loz	3-State Output Leakage			0		±5.0	μΑ
		Data Outputs B _n V _O =0 V or 3.6 V, /OE=GND	0	3.60		±5.0	
ICCA/B	Quiescent Supply Current ^(6, 7)	V _I =V _{CCI} or GND; l _O =0, /OE=GND	1.10 to 3.60	1.10 to 3.60		10.0	μΑ
lccz	Current ^(6, 7)	V _I =V _{CCI} or GND; I _O =0, /OE=V _{IH}	1.10 to 3.60	1.10 to 3.60		10.0	μΑ
loca		V _I =V _{CCB} or GND; I _O =0 B-to-A Direction,	0	1.10 to 3.60		-10.0	μΑ
IOUA	Quiescent Supply	/OE=GND	1.10 to 3.60	0		10.0	μπ
Іссв	Current	V _I =V _{CCA} or GND; I _O =0, A-to-B Direction,	1.10 to 3.60	0		-10.0	μΑ
-505		/OE=GND	0	1.10 to 3.60		10.0	r, ,

Notes:

- 3. This is the output voltage for static conditions. Dynamic drive specifications are given in the Dynamic Output Electrical Characteristics table.
- 4. An external drive must source at least the specified current to switch LOW-to-HIGH.
- 5. An external drive must source at least the specified current to switch HIGH-to-LOW.
- 6. V_{CCI} is the V_{CC} associated with the input side.
- 7. Reflects current per supply, V_{CCA} or V_{CCB}.

Dynamic Output Electrical Characteristic

A Port (A_n)

Output Load: $C_L=15$ pF, $R_L \ge M\Omega$ ($C_{I/O}=4$ pF), $T_A=-40$ to $85^{\circ}C$

Symbol	Parameter	V _{CCA} =3.0 V to 3.6 V		V _{CCA} =2.3 V to 2.7 V		V _{CCA} =1.65 V to 1.95 V		V _{CCA} =1.4 V to 1.6 V		V _{CCA} =1.1 V to 1.3 V	Units
		Тур.	Max.	Тур.	Max.	Тур.	Max	Тур.	Max.	Тур.	
t _{rise}	Output Rise Time A Port ⁽ 9)		3.0		3.5		4.0		5.0	7.5	ns
t _{fall}	Output Fall Time A Port ⁽¹⁰⁾		3.0		3.5		4.0		5.0	7.5	ns
Юнр	Dynamic Output Current High ⁽⁹⁾	-11.4		-7.5		-4.7		-3.2		-1.7	mA
ЮЦД	Dynamic Output Current Low ⁽¹⁰⁾	+11.4		+7.5		+4.7		+3.2		+1.7	mA

B Port (B_n)

Output Load: $C_L=15$ pF, $R_L \ge M\Omega$ ($C_{I/O}=5$ pF), $T_A=-40$ to $85^{\circ}C$

Symbol	Parameter	V _{CCB} =3.0 V to 3.6 V		V _{CCB} =2.3 V to 2.7 V		V _{CCB} =1.65 V to 1.95 V		V _{CCB} =1.4 V to 1.6 V		V _{CCB} =1.1 V to 1.3 V	Units
		Тур.	Max.	Тур.	Max.	Тур.	Max	Тур.	Max.	Тур.	
t _{rise}	Output Rise Time B Port ⁽ 9)		3.0		3.5		4.0		5.0	7.5	ns
t _{fall}	Output Fall Time B Port ⁽¹⁰⁾		3.0		3.5		4.0		5.0	7.5	ns
Юна	Dynamic Output Current High ⁽⁹⁾	-12.0		-7.9		-5.0		-3.4		-1.8	mA
ЮLD	Dynamic Output Current Low ⁽¹⁰⁾	+12.0		+7.9		+5.0		+3.4		+1.8	mA

Notes:

- 8. Dynamic output characteristics are guaranteed, but not tested.
- 9. See Figure 7.
- 10. See Figure 8.

AC Characteristics

$V_{CCA} = 3.0 \text{ V to } 3.6 \text{ V}, T_A = -40 \text{ to } 85^{\circ}\text{C}$

Symbol	Parameter	V _{CCB} =3.0 V to 3.6 V			V _{CCB} =2.3 V to 2.7 V		V _{CCB} =1.65 V to 1.95 V		:1.4 V .6 V	V _{CCB} =1.1 V to 1.3 V	Units
		Min.	Max.	Min.	Max.	Min.	Max	Min.	Max.	Тур.	
t _{PLH} ,t _{PHL}	A to B	0.2	3.5	0.3	3.9	0.5	5.4	0.6	6.8	10.0	ns
TPLH, TPHL	B to A	0.2	3.5	0.2	3.8	0.3	5.0	0.5	6.0	7.0	ns
t _{PZL} ,t _{PZH}	/OE to A, /OE to B		1.7		1.7		1.7		1.7	1.7	μs
tskew	A Port, B Port ⁽¹¹⁾		0.5		0.5		0.5		1.0	1.0	ns

$V_{CCA} = 2.3 \text{ V to } 2.7 \text{ V}, T_A = -40 \text{ to } 85^{\circ}\text{C}$

Symbol	Parameter	V _{CCB} =3.0 V to 3.6 V		V _{CCB} =2.3 V to 2.7 V		V _{CCB} =1.65 V to 1.95 V		V _{CCB} =1.4 V to 1.6 V		V _{CCB} =1.1 V to 1.3 V	Units
		Min.	Max.	Min.	Max.	Min.	Max	Min.	Max.	Тур.	
tour tour	A to B	0.2	3.8	0.4	4.2	0.5	5.6	0.8	6.9	10.5	ns
t _{PLH} ,t _{PHL}	B to A	0.3	3.9	0.4	4.2	0.5	5.5	0.5	6.5	7.0	ns
t _{PZL} ,t _{PZH}	/OE to A, /OE to B		1.7		1.7		1.7		1.7	1.7	μs
tskew	A Port, B Port ⁽¹¹⁾		0.5		0.5		0.5		1.0	1.0	ns

$V_{CCA} = 1.65 \text{ V to } 1.95 \text{ V}, T_A = -40 \text{ to } 85^{\circ}\text{C}$

Symbol	Parameter	V _{CCB} =3.0 V to 3.6 V			V _{CCB} =2.3 V to 2.7 V		1.65 V .95 V	V _{CCB} =1.4 V to 1.6 V		V _{CCB} =1.1 V to 1.3 V	Units
		Min.	Max.	Min.	Max.	Min.	Max	Min.	Max.	Тур.	
tou tou	A to B	0.3	5.0	0.5	5.5	0.8	6.7	0.9	7.5	11.0	ns
t _{PLH} ,t _{PHL}	B to A	0.5	5.4	0.5	5.6	8.0	6.7	1.0	7.0	7.0	ns
t _{PZL} ,t _{PZH}	/OE to A, /OE to B		1.7		1.7		1.7		1.7	1.7	μs
tskew	A Port, B Port ⁽¹¹⁾		0.5		0.5		0.5		1.0	1.0	ns

Note

11. Skew is the variation of propagation delay betw een output signals and applies only to output signals on the same port $(A_n \text{ or } B_n)$ and switching with the same polarity (LOW-to-HIGH or HIGH-to-LOW) (see Figure 10). Skew is guaranteed, but not tested.

AC Characteristics (Continued)

$V_{CCA} = 1.4 \text{ V to } 1.6 \text{ V}, T_{A} = -40 \text{ to } 85^{\circ}\text{C}$

Symbol	Parameter	V _{CCB} =3.0 V to 3.6 V		V _{CCB} =2.3 V to 2.7 V		V _{CCB} =1.65 V to 1.95 V		V _{CCB} =1.4 V to 1.6 V		V _{CCB} =1.1 V to 1.3 V	Units
		Min.	Max.	Min.	Max.	Min.	Max	Min.	Max.	Тур.	
t _{PLH} ,t _{PHL}	A to B	0.5	6.0	0.5	6.5	1.0	7.0	1.0	8.5	11.5	ns
	B to A	0.6	6.8	8.0	6.9	0.9	7.5	1.0	8.5	9.0	ns
t _{PZL} ,t _{PZH}	/OE to A, /OE to B		1.7		1.7		1.7		1.7	1.7	μs
tskew	A Port, B Port ⁽¹²⁾		1.0		1.0		1.0		1.0	1.0	ns

$V_{CCA} = 1.1 \text{ V to } 1.3 \text{ V}, T_A = -40 \text{ to } 85^{\circ}\text{C}$

Symbol	Parameter	V _{CCB} =3.0 V to 3.6 V	V _{CCB} =2.3 V to 2.7 V	V _{CCB} =1.65 V to 1.95 V	V _{CCB} =1.4 V to 1.6 V	V _{CCB} =1.1 V to 1.3 V	Units
		Тур.	Тур.	Тур.	Тур.	Тур.	
4	A to B	7.1	6.5	7.0	7.1	13.5	ns
t _{PLH} ,t _{PHL}	B to A	10.3	10.5	10.8	11.3	13.5	ns
1 '	/OE to A, /OE to B	1.7	1.7	1.7	1.7	1.7	μs
tskew	A Port, B Port ⁽¹²⁾	1.0	1.0	1.0	1.0	1.0	ns

Note:

^{12.} Skew is the variation of propagation delay between output signals and applies only to output signals on the same port (An or Bn) and switching with the same polarity (LOW-to-HIGH or HIGH-to-LOW) (see Figure 10). Skew is guaranteed, but not tested.

Maximum Data Rate

$T_A=-40$ to 85° C.

V _{CCA}	V _{CCB} =3.0 V to 3.6 V	V _{CCB} =2.3 V to 2.7 V	V _{CCB} =1.65 V to 1.95 V	V _{CCB} =1.4 V to 1.6 V	V _{CCB} =1.1V to 1.3 V	Units
	Min.	Min.	Min.	Min.	Тур.	
V _{CCA} =3.00 V to 3.60 V	140	120	100	80	40	Mbps
V _{CCA} =2.30 V to 2.70 V	120	120	100	80	40	Mbps
V _{CCA} =1.65 V to 1.95 V	100	100	80	60	40	Mbps
V _{CCA} =1.40 V to 1.60 V	80	80	60	60	40	Mbps
V _{CCA} =1.10 V to 1.30 V	Тур.	Тур.	Тур.	Тур.	Тур.	
V CCA=1.10 V to 1.00 V	40	40	40	40	40	Mbps

Notes:

- 13. Maximum data rate is guaranteed, but not tested.
- 14. Maximum data rate is specified in megabits per second (see Figure 9). It is equivalent to two times the F-toggle frequency, specified in megahertz. For example, 100 Mbps is equivalent to 50 MHz.

Capacitance

Symbol	Parameter		Conditions	T _A =+25°C Typical	Units
C _{IN}	Input Capacitance Control Pir	n (/OE)	V _{CCA} =V _{CCB} =GND	3	pF
C _{I/O}	Input / Output Capacitance	An	Vcca=Vccb=3.3V,/OE=Vcca	4	pF
OI/O	G/O Imput / Output Capacitance		VCCA-VCCB-0.0 V,/OL-VCCA	5	Pi
C _{pd}	Pow er Dissipation Capacitano	се	$V_{CCA}=V_{CCB}=3.3 \text{ V}, V_{I}=0 \text{ V or } V_{CC},$ f=10 MHz	25	pF

I/O Architecture Benefit

The FXLA102 I/O architecture benefits the end user, beyond level translation, in the following three ways:

Auto Direction without an external direction pin.

Drive Capacitive Loads. Automatically shifts to a higher current drive mode only during "Dynamic Mode" or HL / LH transitions.

Lower Power Consumption. Automatically shifts to low-power mode during "Static Mode" (no transitions), lowering power consumption.

The FXLA102 does not require a direction pin. Instead, the VO architecture detects input transitions on both side and automatically transfers the data to the corresponding output. For example, for a given channel, if both A and B side are at a static LOW, the direction has been established as A \rightarrow B, and a LH transition occurs on the B port; the FXLA102 internal VO architecture automatically changes direction from A \rightarrow B to B \rightarrow A.

During HL / LH transitions, or "Dynamic Mode," a strong output driver drives the output channel in parallel with a weak output driver. After a typical delay of approximately 10 ns - 50 ns, the strong driver is turned off, leaving the weak driver enabled for holding the logic state of the channel. This weak driver is called the "bus

hold." "Static Mode" is when only the bus hold drives the channel. The bus hold can be over ridden in the event of a direction change. The strong driver allows the FXLA102 to quickly charge and discharge capacitive transmission lines during dynamic mode. Static mode conserves pow er, where l_{CC} is typically $<5~\mu\text{A}$.

Bus Hold Minimum Drive Current

Specifies the minimum amount of current the bus hold driver can source/sink. The bus hold minimum drive current (II_{HOLD}) is V_{CC} dependent and guaranteed in the DC Electrical tables. The intent is to maintain a valid output state in a static mode, but that can be overridden when an input data transition occurs.

Bus Hold Input Overdrive Drive Current

Specifies the minimum amount of current required (by an external device) to overdrive the bus hold in the event of a direction change. The bus hold overdrive (II_{ODH} , II_{ODL}) is V_{CC} dependent and guaranteed in the DC Electrical tables.

Dynamic Output Current

The strength of the output driver during LH / HL transitions is referenced on page 8, Dynamic Output Electrical Characteristics, I_{OHD}, and I_{OLD}.

Test Diagrams

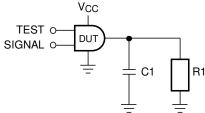


Figure 3. Test Circuit

Table 1. AC Test Conditions

Test	Input Signal	Output Enable Control
tplн, tpнL	Data Pulses	0 V
tpzL	0 V	HIGH to LOW Switch
tрzн	V _{CCI}	HIGH to LOW Switch

Table 2. AC Load

V _{cco}	C1	R1
1.2 V± 0.1 V	15 pF	1 ΜΩ
1.5 V± 0.1 V	15 pF	1 ΜΩ
1.8 V ± 0.15 V	15 pF	1 ΜΩ
2.5 V ± 0.2 V	15 pF	1 ΜΩ
3.3 V ± 0.3 V	15 pF	1 ΜΩ

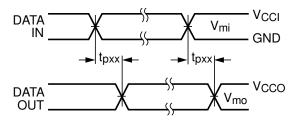


Figure 4. Waveform for Inverting and Non-Inverting Functions

Notes:

- 15. Input $t_R = t_F = 2.0 \text{ ns}$, 10% to 90%.
- 16. Input $t_R = t_F = 2.5$ ns, 10% to 90%, at $V_I = 3.0$ V to 3.6 V only.

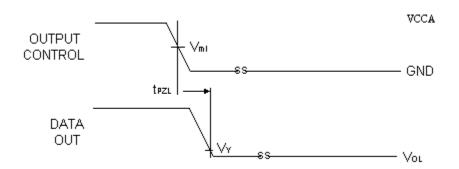


Figure 5. 3-State Output Low Enable Time

Notes:

- 17. Input $t_R = t_F = 2.0$ ns, 10% to 90%.
- 18. Input $t_R = t_F = 2.5$ ns, 10% to 90%, at $V_I = 3.0$ V to 3.6 V only.

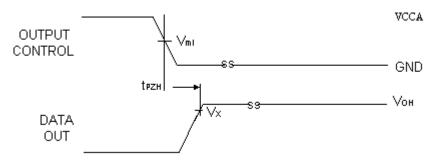


Figure 6. 3-State Output High Enable Time

Notes:

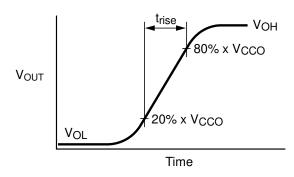
- 19. Input $t_R = t_F = 2.0$ ns, 10% to 90%.
- 20. Input $t_R = t_F = 2.5$ ns, 10% to 90%, at $V_I = 3.0$ V to 3.6 V only.

Table 3. Test Measure Points

Symbol	V _{cc}
V _{MI} ⁽²¹⁾	V _{CCI} /2
V _{MO}	V _{CCo} /2
Vx	0.9 x V _{CCo}
Vy	0.1 x V _{CCo}

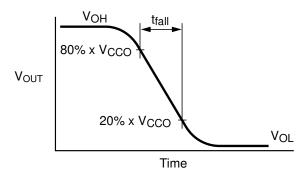
Note:

21. $V_{CCI}=V_{CCA}$ for control pin /OE or $V_{MI}=(V_{CCA}/2)$.



$$I_{O\!H\!D} \approx (C_L + C_{I/O}) \times \frac{\Delta V_{O\!U\!T}}{\Delta t} = (C_L + C_{I/O}) \times \frac{(20\% - 80\%) \bullet V_{C\!C\!O}}{t_{R\!I\!S\!E}}$$

Figure 7. Active Output Rise Time and Dynamic Output Current High



$$I_{OLD} \approx (C_L + C_{I/O}) \times \frac{\Delta V_{OUT}}{\Delta t} = (C_L + C_{I/O}) \times \frac{(80\% - 20\%) \bullet V_{CCO}}{t_{FALI}}$$

Figure 8. Active Output Fall Time and Dynamic Output Current Low

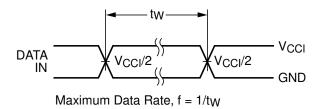


Figure 9. Maximum Data Rate

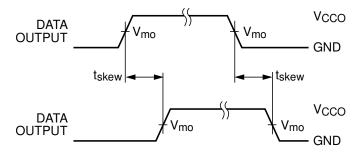
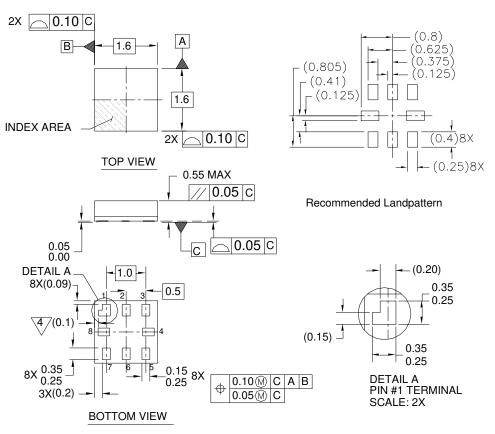


Figure 10. Output Skew Time

Note:

22. $t_{SKEW} = (t_{pHLmax} - t_{pHLmin})$ or $(t_{pLHmax} - t_{pLHmin})$

Physical Dimensions



Notes:

- 1. PACKAGE CONFORMS TO JEDEC MO-255 VARIATION UAAD
- 2. DIMENSIONS ARE IN MILLIMETERS
- 3. DRAWING CONFORMS TO ASME Y.14M-1994
- 4, PIN 1 FLAG, END OF PACKAGE OFFSET
- 5. DRAWING FILE NAME: MKT-MAC08AREV4

MAC08AREV4

Figure 11.8-Lead, MicroPak™, 1.6mm Wide

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